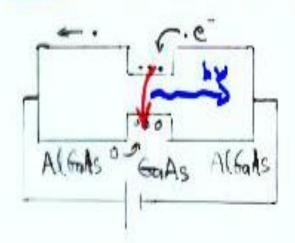
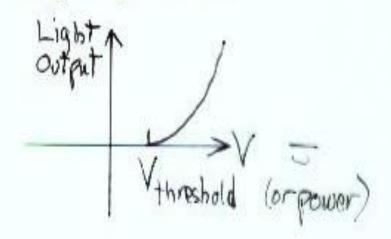
6.3 Diodes for Light Emitters
· LED : (light emitting diodes)
LED: (light emitting diodes) lasers (light amplification by stimulated emissions of radiation)
Forward bias injection: Electro luminescence
hum
ager - Narrower linewidth emission ("monochromatic")
-> Directional
-> Directional -> Coherent (Plane waves in phase) >> >> >> >> >> >> >> >> >> >> >> >> >>
semiconductors for lasers need:
Direct gap (efficient recombination)
→K

. Match 2 to low absorption for fibers.





Reduce VThreshold or Jthreshold

to Shrink power supply required

Light Emitting Diode - Heterostructures

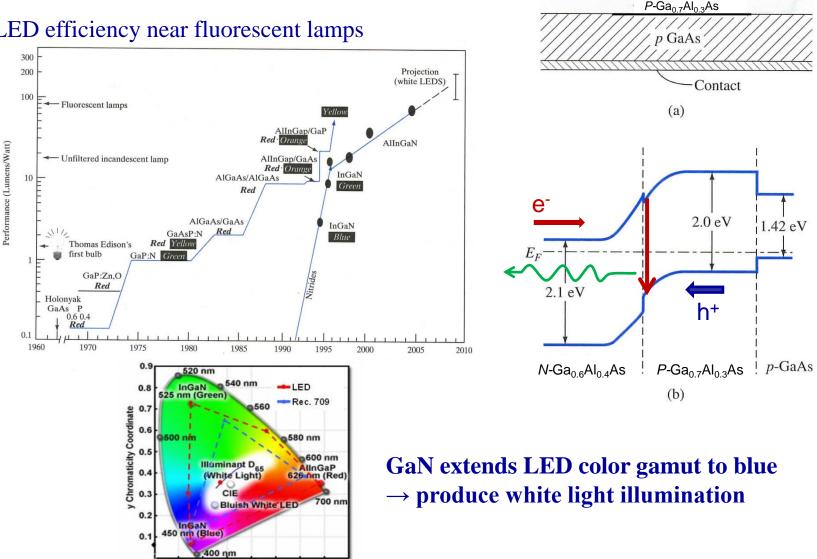
Contact

N-Ga_{0.6}Al_{0.4}As

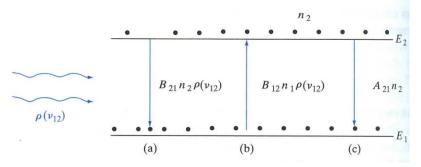
Electrons inserted from wide band gap N-Ga_{0.6}Al_{0.4}As in narrower bandgap p-Ga_{0.7}Al_{0.3}As

0.2 0.3 0.4 0.5 0.6 x Chromaticity Coordinate

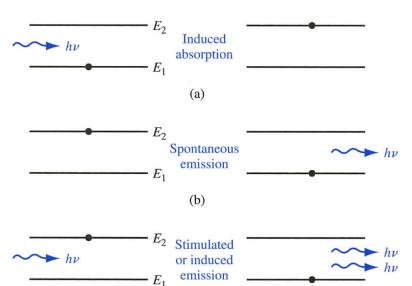
LED efficiency near fluorescent lamps



Stimulated Emission - Lasers



Spontaneous emission proportional to upper level population



$$B_{12} n_1 p(v_{12}) = A_{21} n_2 + B_{21} n_2 \rho(v_{12}) \rightarrow \text{Einstein Coefficients}$$

emission emission

$$\frac{\text{Stimulated emission rate}}{\text{Spontaneous emission rate}} = \frac{B_{21}n_2\rho(v_{12})}{A_{21}n_2} = \frac{B_{21}}{A_{21}}\rho(v_{12})$$

$$\frac{\text{Stimulated emission rate}}{\text{Absorption rate}} = \frac{B_{21}n_2\rho(v_{12})}{B_{12}n_1\rho(v_{12})} = \frac{B_{21}}{B_{12}} \frac{n_2}{n_1}$$

To get stimulated emission > absorption, need $n_2 > n_1$

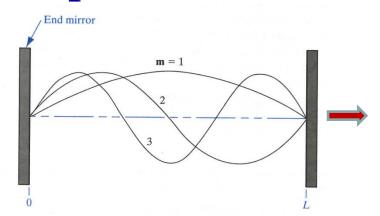
But $n_2/n_1 < 1$ in equilibrium \rightarrow For $n_2/n_1 > 1$, need "population inversion"

- (1) Optical resonant cavity to build up photon field
- (2) Means to obtain population inversion

Stimulated Emission – Build Up Photon Field

Resonant modes in a laser cavity: Cavity length $L = m\lambda/2$; Reflecting mirrors – partially transmitting (small)

 \rightarrow Build up $\rho_{12}(v_{12})$



Stimulated Emission – Maintain Population Inversion

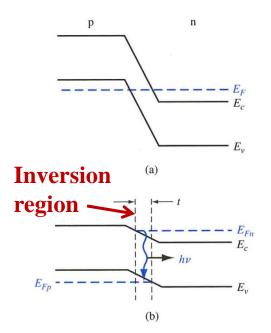


Figure 14.33 I (a) Degenerately doped pn junction at zero bias. (b) Degenerately doped pn junction under forward bias with photon emission.

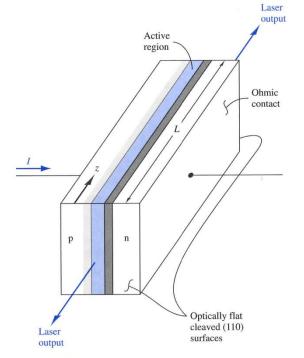


Figure 14.34 | A pn junction laser diode with cleaved (110) planes forming the Fabry-Perot cavity. (After Yang [22].)

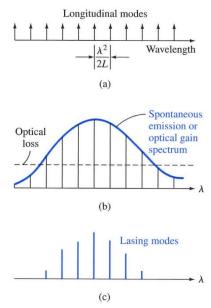
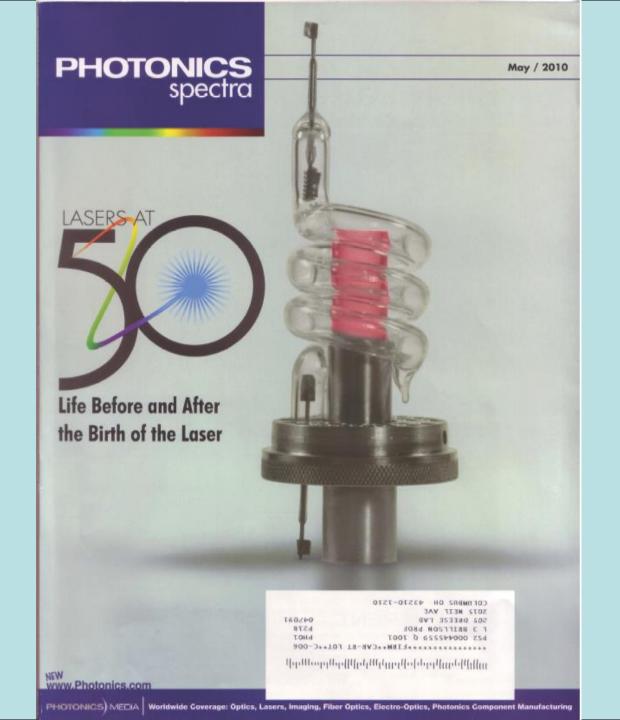


Figure 14.35 | Schematic diagram showing (a) resonant modes of a cavity with length L, (b) spontaneous emission curve, and (c) actual emission modes of a laser diode. (After Yang [22].)



Population Inversion at a Junction

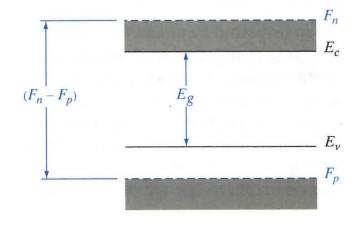
Recall quasi-Fermi levels:

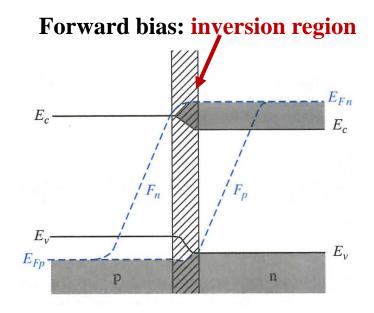
Measure of departure from equilibrium

$$n = N_c e^{-(Ec - Fn)/kT} = n_i e^{(Fn - Ei)/kT}$$

$$p = N_v e^{-(Fp - Ev)/kT} = n_i e^{(Ei - Fp)/kT}$$

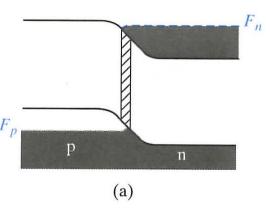
Inversion region expanded

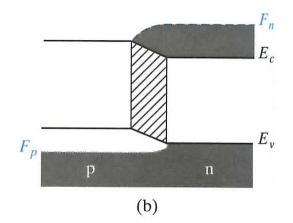




Population inversion exists when $F_n - F_p > h \upsilon$ Minimum requirement: $F_n - F_p > E_g$

- Inversion region width varies with forward bias
- Range of stimulated emission energies
- Dominant laser transitions ^{F_p}
 determined by resonant
 cavity & band edge





Heterojunction Lasers

Single Heterojunction Laser

Electrons confined to n GaAs p GaAs thin p-GaAs region under bias Equilibrium 2 eV $<1 \mu \text{ m}$ pAlGaAs p GaAs 1.4 eV n GaAs substrate High forward bias (a) 2 eV 1.4 eV (b) K **AlGaAs Index of Refraction** Inversion layer $h\nu = 1.38 \text{ eV}$ 3.5 T = 297 KRefractive index \overline{n} Use AlGaAs for total internal reflection: 3.2 optical confinement 3.1

1.0

AlAs

3.0

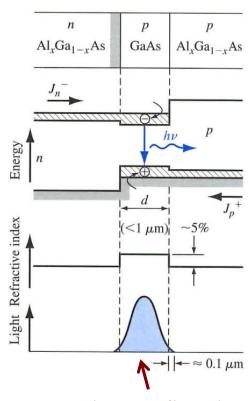
2.9

GaAs

0.5

Mole fraction AlAs, x

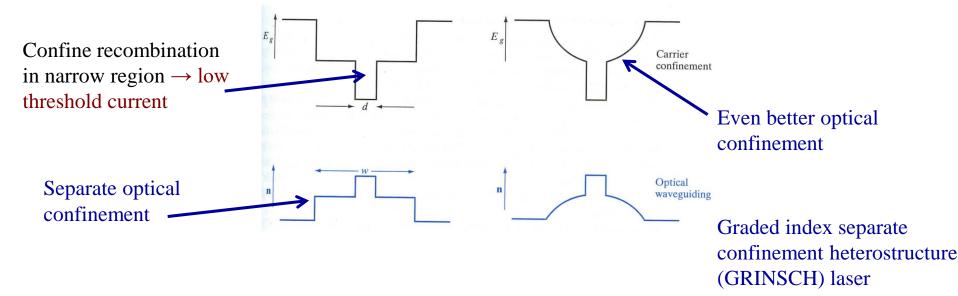
Double Heterojunction Laser



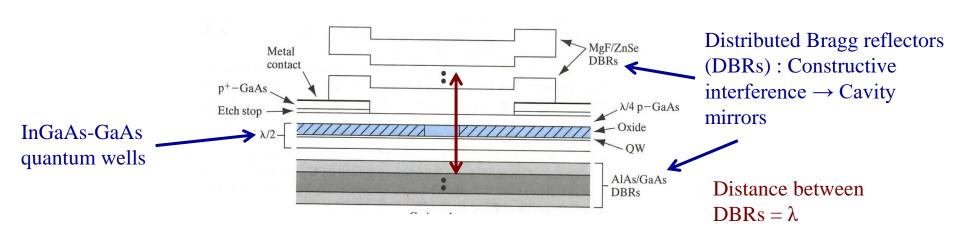
Light confined in dielectric waveguide

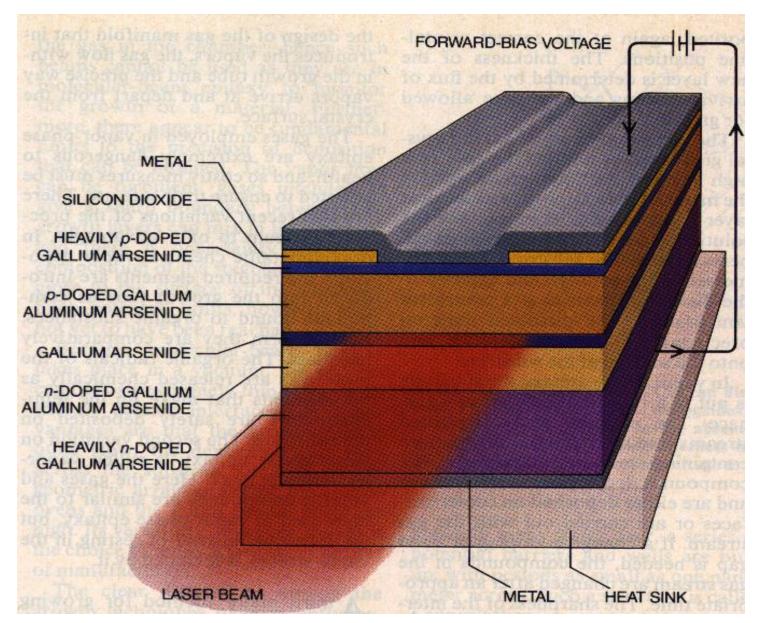
Multilayer Heterostructure Lasers

Separate confinement and graded index channels



Oxide-confined vertical cavity surface-emitting laser (VCSEL) diode





Man-Made Structure of Atomically-Ordered Layers Based on Quantum Mechanical Principles



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photonics.com



hat absorbs all wavelengths of light, didn't radiate all frequencies of light equally when heated.



History Of The Laser A Trip Through The Light Fantastic Nelinda Rose, Senior Editor, melinda.rose@photonics.com

HISTORY OF THE LASER

Share

n honor of the laser turning 50, here is a timeline of some of the more notable scientific accomplishments elated to light amplification by stimulated emission of radiation (laser). An interactive version is available at ww.lasertimeline.com. The laser would not have been possible without an understanding that light is a form of lectromagnetic radiation. Max Planck received the Nobel Prize in physics in 1918 for his discovery of elementary nergy quanta. Planck was working in thermodynamics, trying to explain why "blackbody" radiation, something

VIDEO

WHITEPAPERS

First LED Replacement Bulb Unveiled

New Cell Phone App: Night Vision

Long-Lost Lunar Reflector Located

Images of Atomic Spin Captured

Tabletop 3-D System to Print in Glass

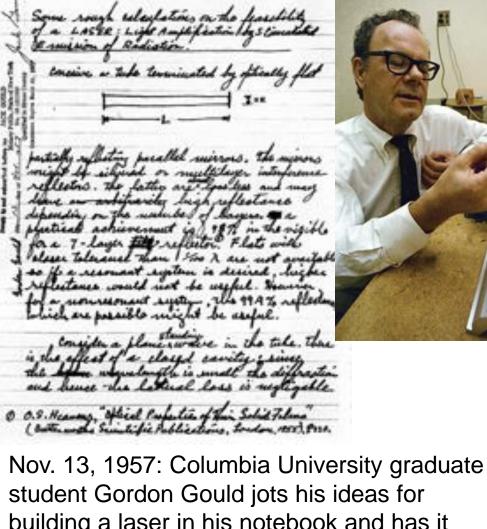
Max Planck

In his most important work, published in 1900, Planck deduced the releasinship between energy and the frequency of radiation, essentially saying that energy could be emitted or absorbed only in discrete chunks - which he called quanta - even if the chunks were very small. His theory marked a turning point in physics and inspired up-and-coming physicists such as Albert Einstein. In 1905, Einstein released his paper on the photoelectric effect, which proposed that light also delivers its energy in chunks, in this case discrete quantum particles now called photons.



Clear Multiwave Nd:YAG • KTP • Alex • Diode • CO2 • Holmium FREE design consultation on all of our custom eyewear! Innovative Clear Lens Multi-Laser Tecnology

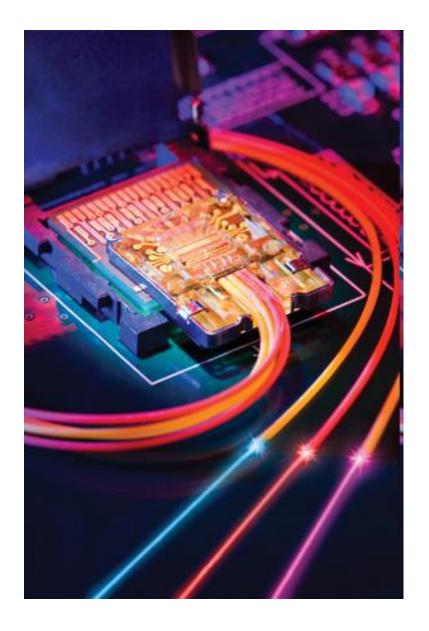
hysicists John L. Emmett (left) and John H. Nuckolls were the key Lawrence ivermore National Laboratory pioneers in laser and fusion science and echnology. Emmett co-invented the multipass laser architecture still in use





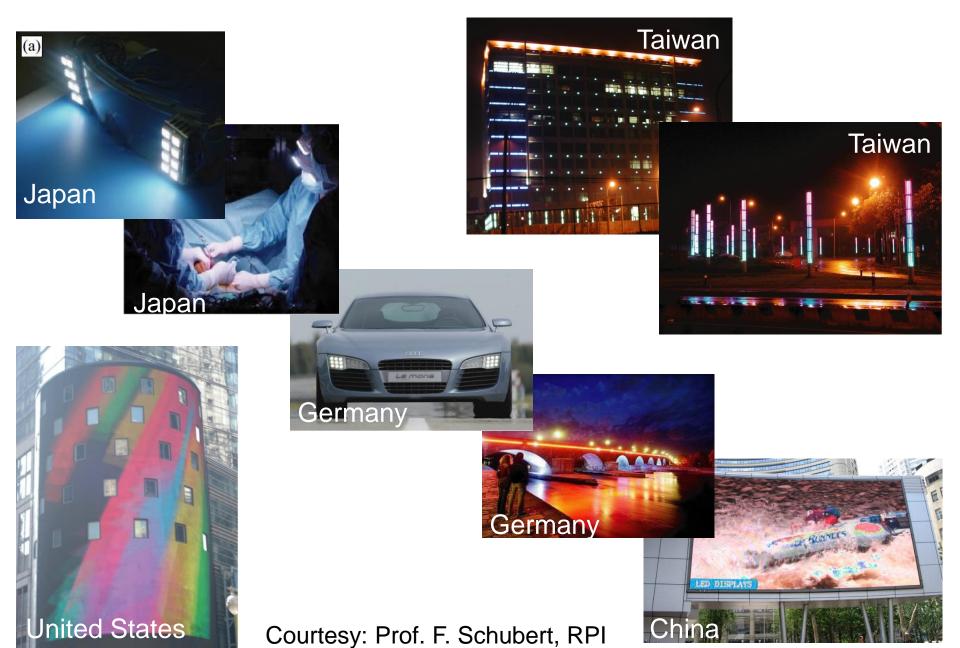
Nov. 13, 1957: Columbia University graduate student Gordon Gould jots his ideas for building a laser in his notebook and has it notarized at a candy store in the Bronx. It is considered the first use of the acronym laser. Gould leaves the university a few months later to join private research company TRG (Technical Research Group).

March 22, 1960: Townes and Schawlow, under Bell Labs, are granted US patent number 2,929,922 for the optical maser, now called a laser. With their application denied, Gould and TRG launch what would become a 30-year patent dispute related to laser invention.



Light Peak module close-up with laser light added for illustration (actual infrared light is invisible to the eye).

Recent applications (not all of them are saving power)





From Black Box to Physics of electrons and holes at interfaces.

From le, n, p, T's to equivalent circuit diagrams.

The End



" LOOK, I WOULD SAY TO LEONARDO. 'SEE HOW FAR OUR TECHNOLOGY HAS TAKEN US'. LEONARDO WOULD ANSWER! YOU MUST EXPLAIN TO ME HOW EVERYTHING WORKS."

AT THAT POINT, MY FANTASY ENDS."